

MOSFET

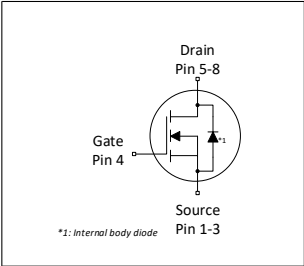
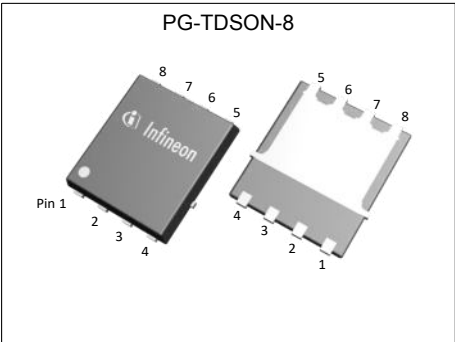
OptiMOS™ Power-MOSFET, 30 V

Features

- Optimized for high performance SMPS
- Integrated monolithic Schottky-like diode
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=4.5\text{ V}$
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(on),max}$	1.1	mΩ
I_D	230	A
Q_{OSS}	45	nC
$Q_G(0V..10V)$	68	nC



Type / Ordering Code	Package	Marking	Related Links
BSC011N03LSI	PG-TDSON-8	011N03LI	-

¹⁾ J-STD20 and JESD22

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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	230 146 197 125 37	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=4.5\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=4.5\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{ K/W}^2)$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	920	A	$T_C=25\text{ °C}$
Avalanche current, single pulse ⁴⁾	I_{AS}	-	-	50	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	100	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	96 2.5	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ K/W}^2)$
Operating and storage temperature	T_J , T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	1.3	K/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	K/W	-
Device on PCB, 6 cm ² cooling area ²⁾	R_{thJA}	-	-	50	K/W	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See figure 3 for more detailed information

⁴⁾ See figure 13 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	$V_{GS}=0\text{ V}$, $I_D=10\text{ mA}$
Breakdown voltage temperature coefficient	$dV_{(BR)DSS}/dT_j$	-	15	-	mV/K	$I_D=10\text{ mA}$, referenced to 25 °C
Gate threshold voltage	$V_{GS(th)}$	1.2	-	2	V	$V_{DS}=V_{GS}$, $I_D=250\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	-	0.5	mA	$V_{DS}=24\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=24\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.2	1.5	m Ω	$V_{GS}=4.5\text{ V}$, $I_D=30\text{ A}$ $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$
Gate resistance	R_G	0.3	0.6	1.2	Ω	-
Transconductance	g_{fs}	80	160	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=30\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	4300	5719	pF	$V_{GS}=0\text{ V}$, $V_{DS}=15\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	1600	2128	pF	$V_{GS}=0\text{ V}$, $V_{DS}=15\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	220	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=15\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	6.4	-	ns	$V_{DD}=15\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	9.2	-	ns	$V_{DD}=15\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	35	-	ns	$V_{DD}=15\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	6.2	-	ns	$V_{DD}=15\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

¹⁾ Defined by design. Not subject to production test

Table 6 Gate charge characteristics¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge ²⁾	Q_{gs}	-	10.1	13.4	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	6.8	-	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate to drain charge ²⁾	Q_{gd}	-	10.6	14	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Switching charge	Q_{sw}	-	13.9	-	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total ²⁾	Q_g	-	34	45	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	2.4	-	V	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total ²⁾	Q_g	-	68	90	nC	$V_{DD}=15\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	27	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Output charge ²⁾	Q_{oss}	-	45	60	nC	$V_{DD}=15\text{ V}$, $V_{GS}=0\text{ V}$

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	120	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	920	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.56	0.7	V	$V_{GS}=0\text{ V}$, $I_F=12\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery charge	Q_{rr}	-	5	-	nC	$V_R=15\text{ V}$, $I_F=12\text{ A}$, $di_F/dt=400\text{ A}/\mu\text{s}$

¹⁾ See "Gate charge waveforms" for parameter definition

²⁾ Defined by design. Not subject to production test

4 Electrical characteristics diagrams

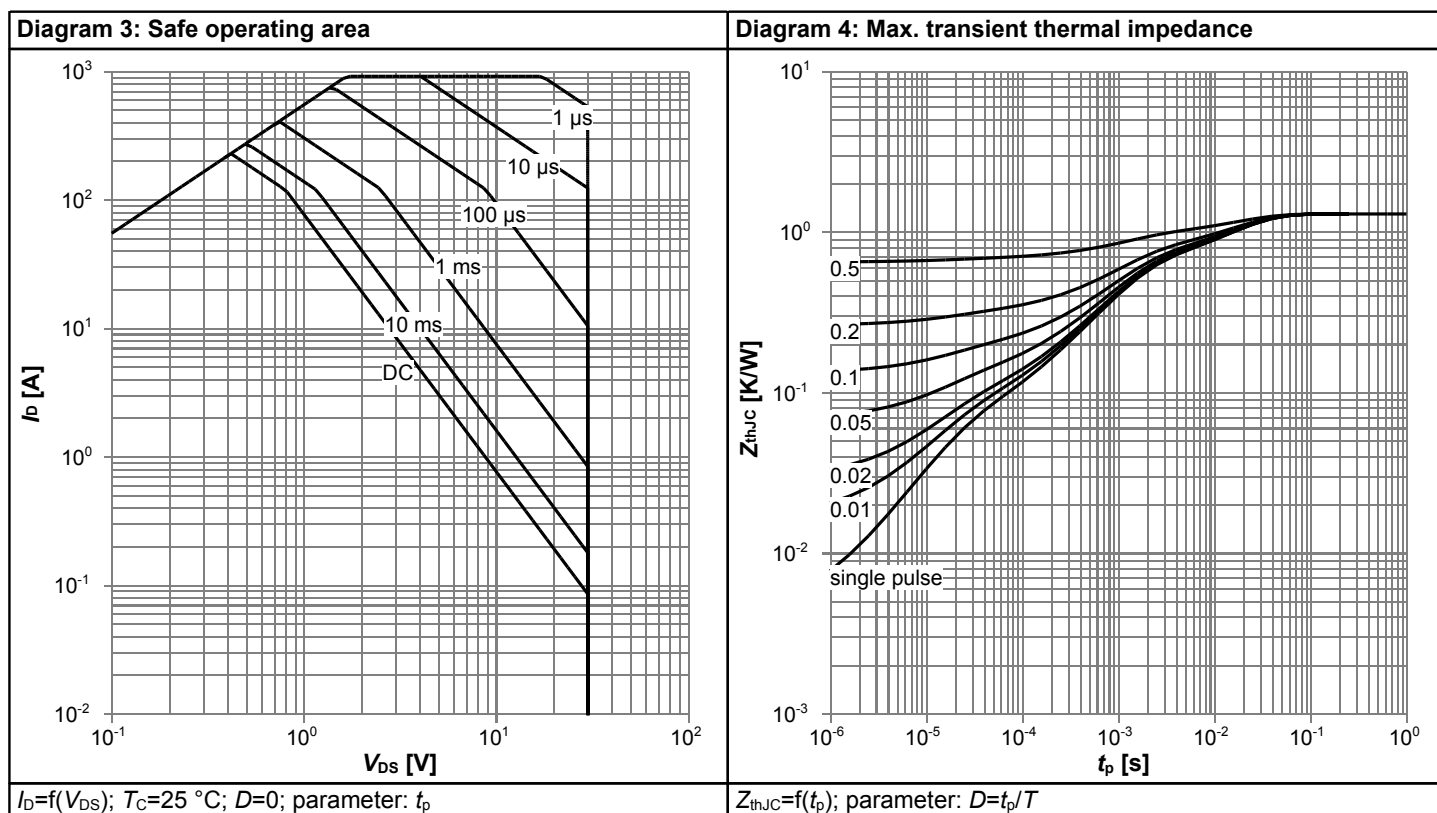
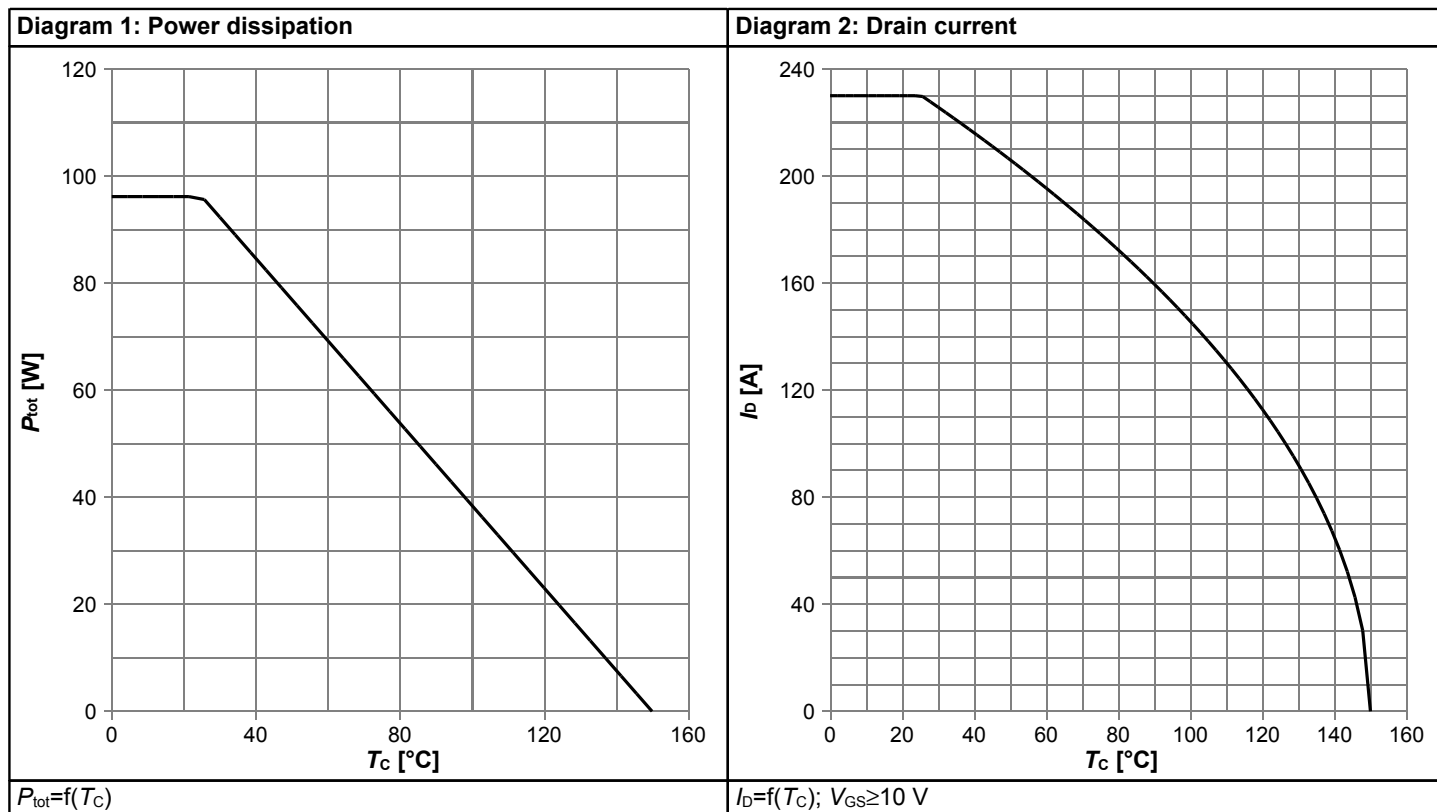
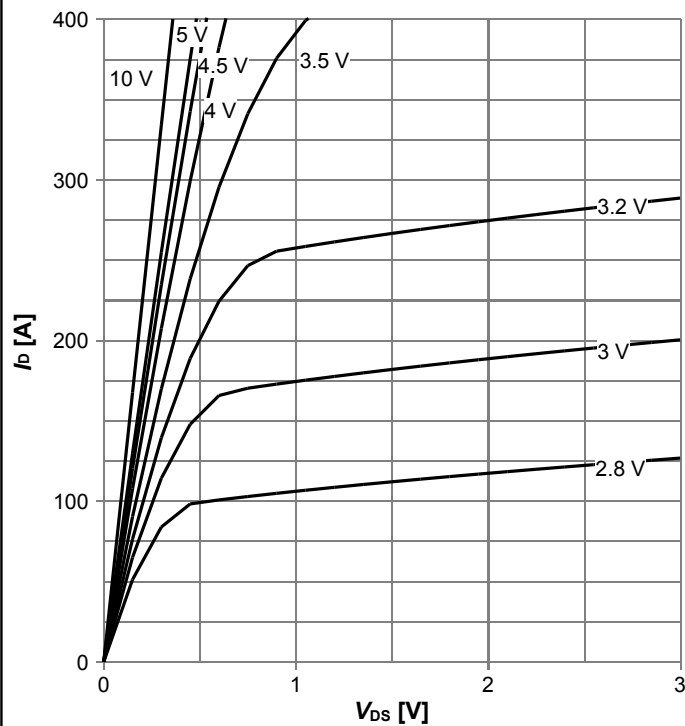
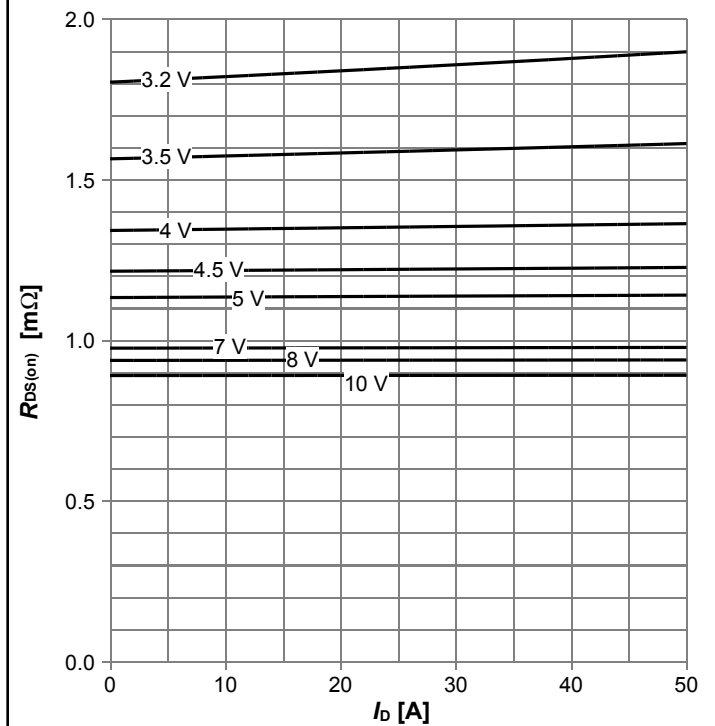


Diagram 5: Typ. output characteristics



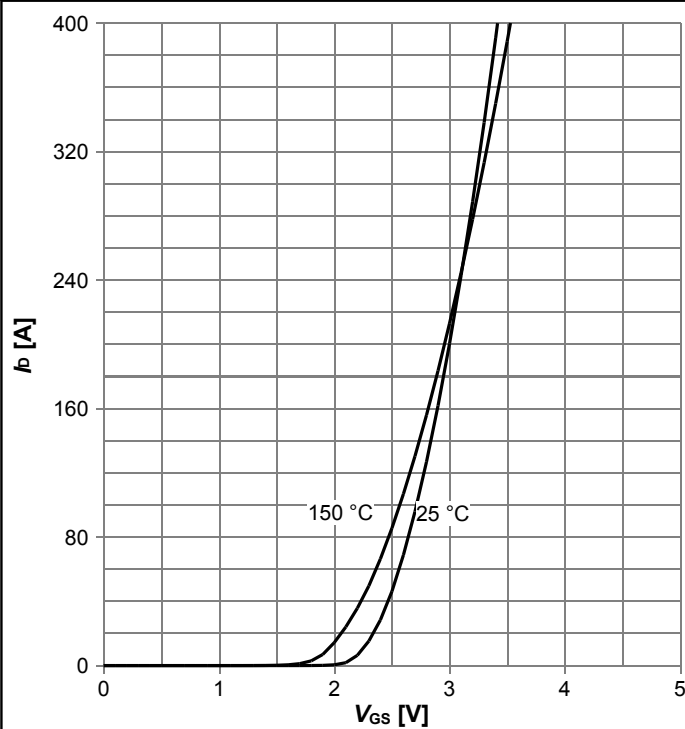
$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



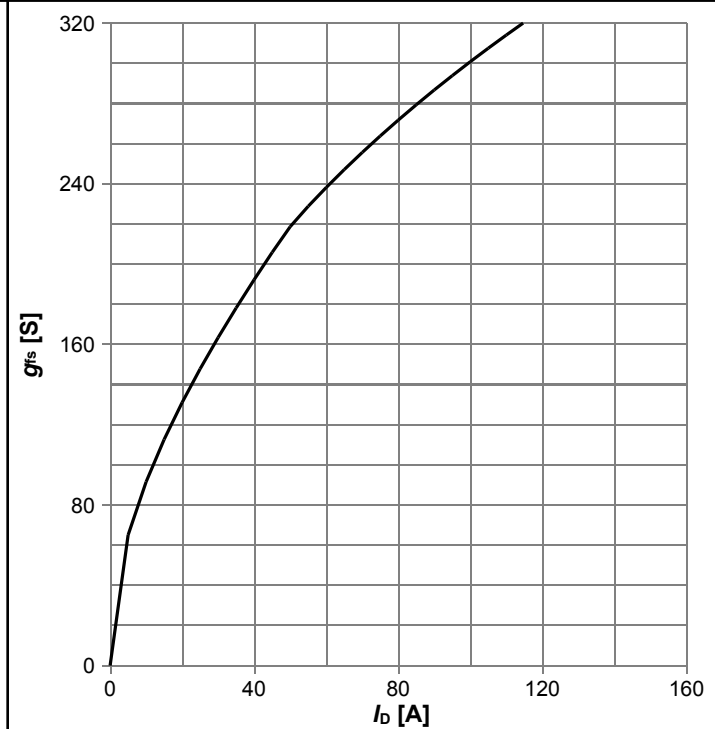
$R_{DS(on)} = f(I_D)$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics

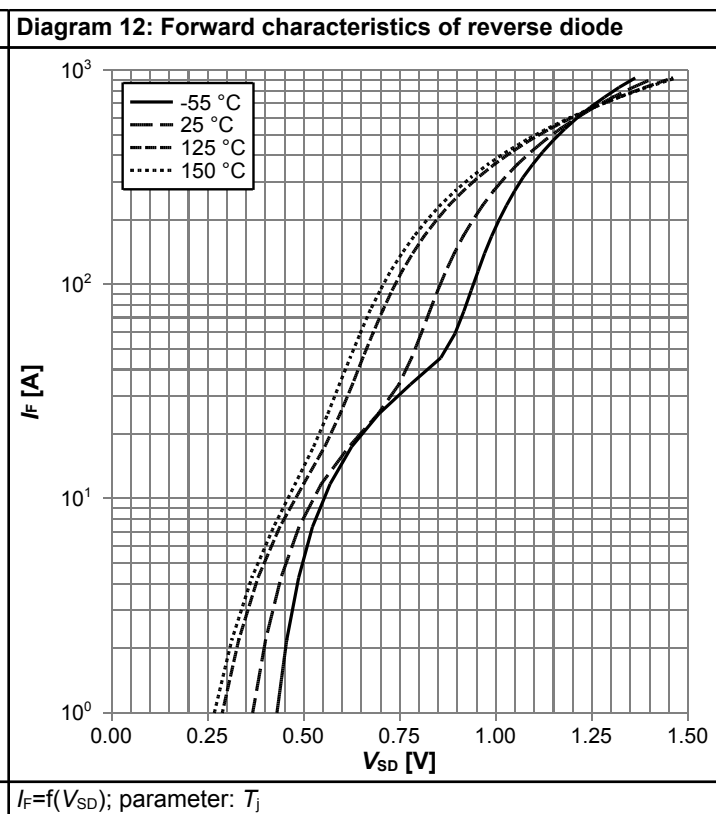
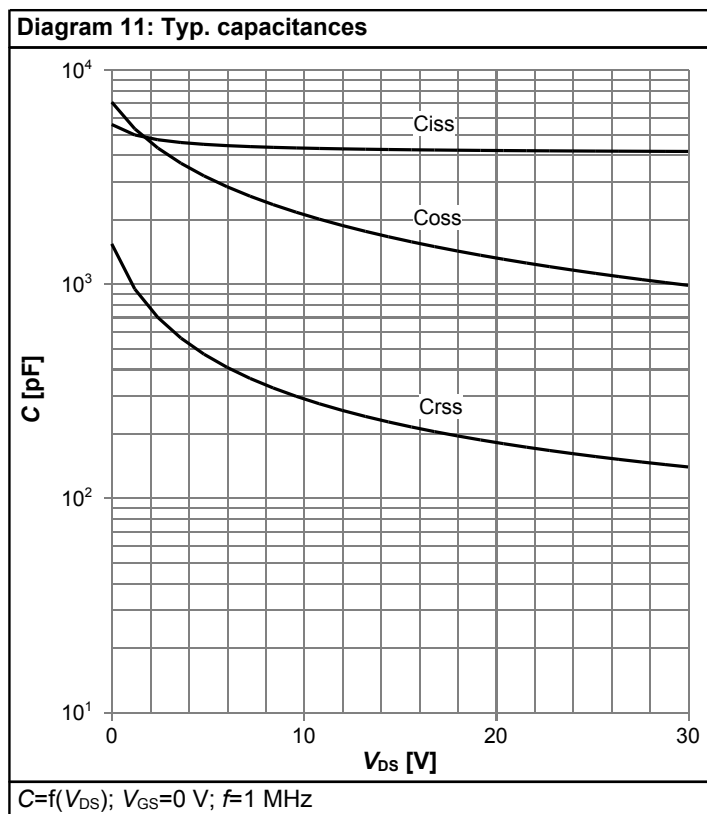
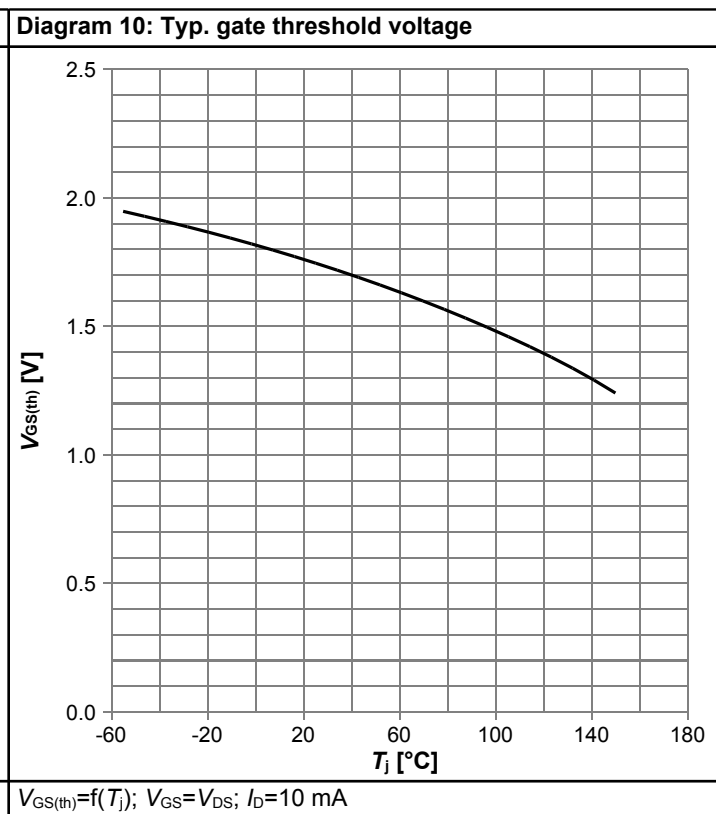
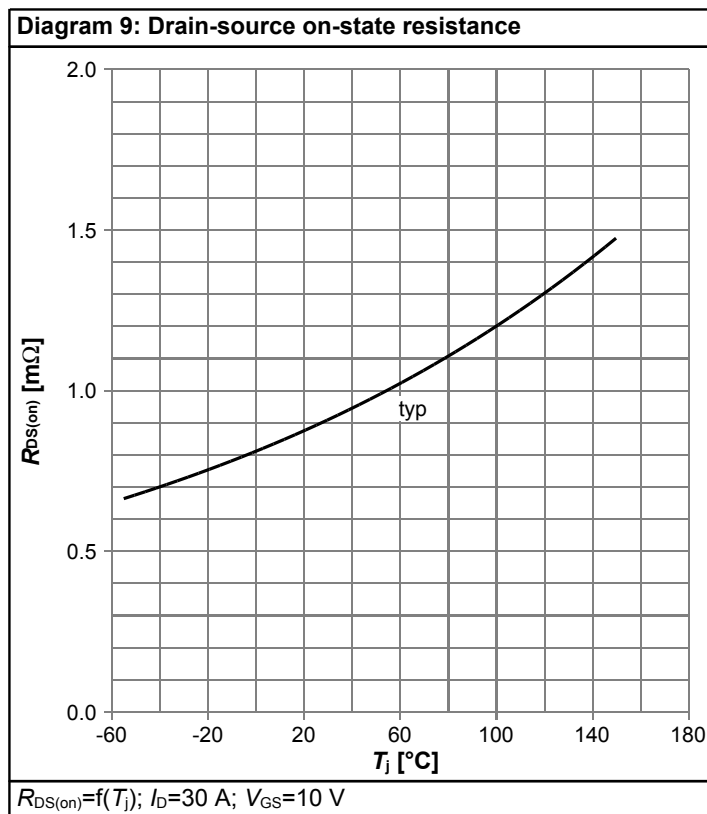


$I_D = f(V_{GS})$; $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



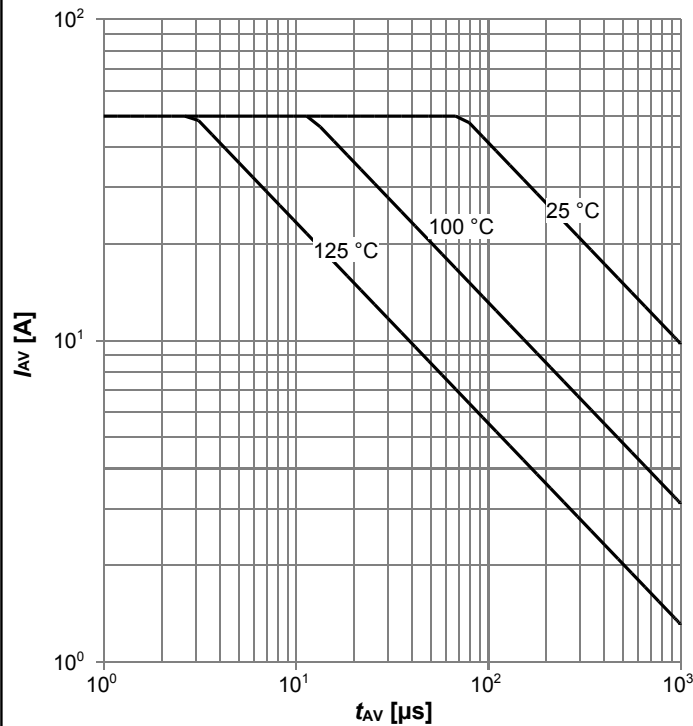
$g_{fs} = f(I_D)$; $T_j = 25^\circ\text{C}$



OptiMOS™ Power-MOSFET, 30 V

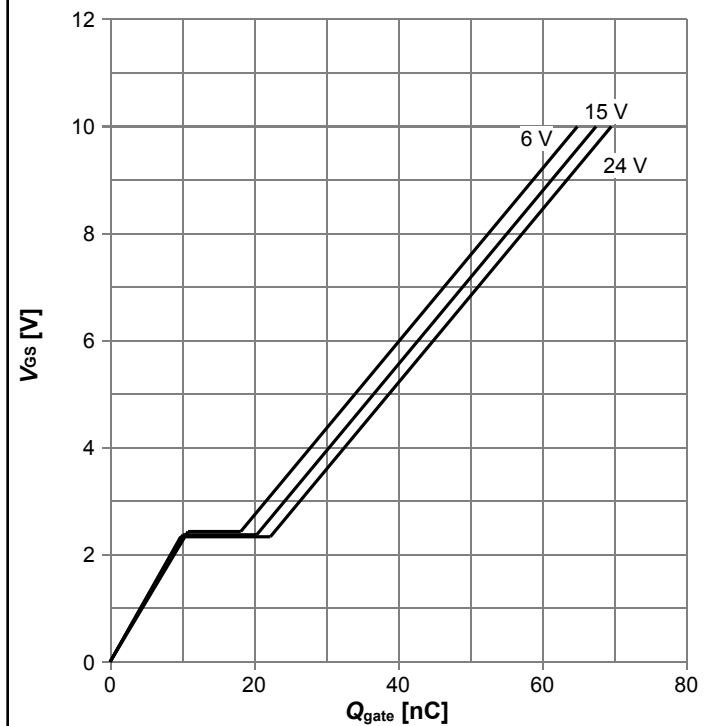
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Diagram 13: Avalanche characteristics



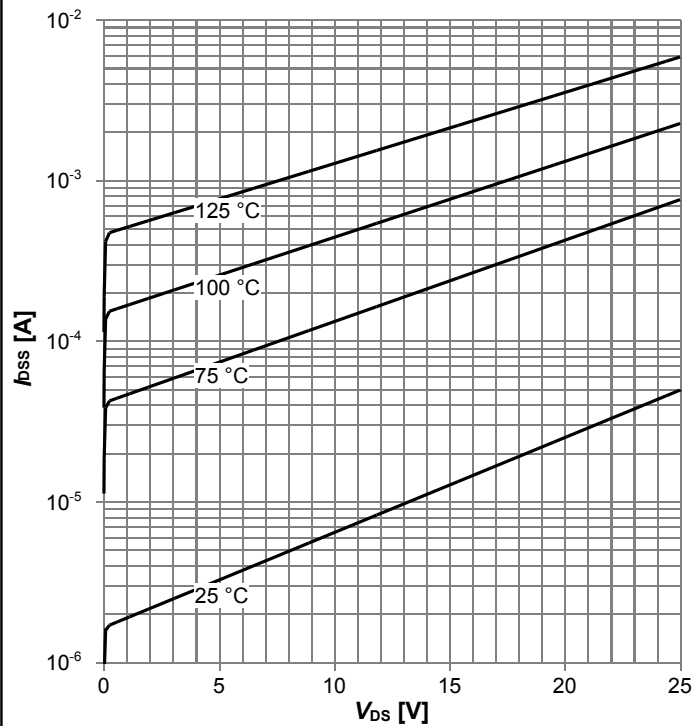
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



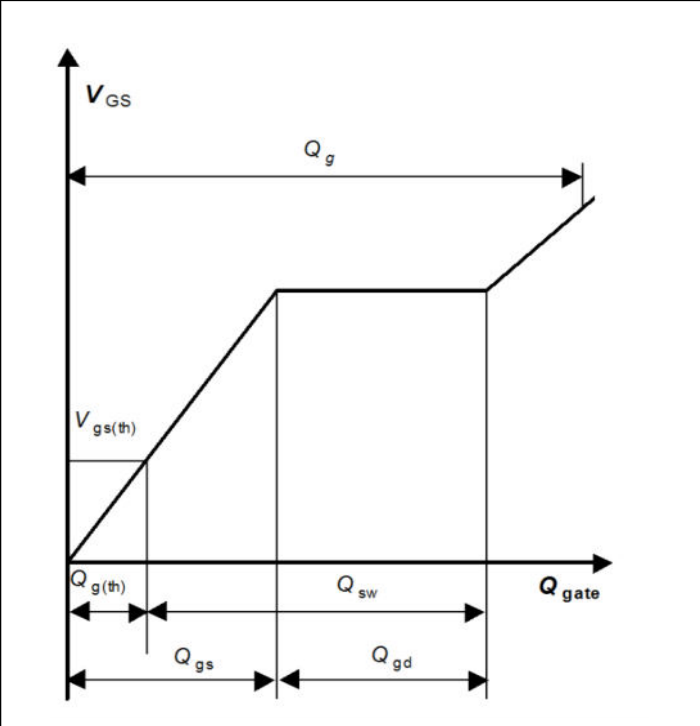
$V_{GS}=f(Q_{gate})$; $I_D=30\text{ A}$ pulsed; parameter: V_{DD}

Diagram 15: Typ. drain-source leakage current

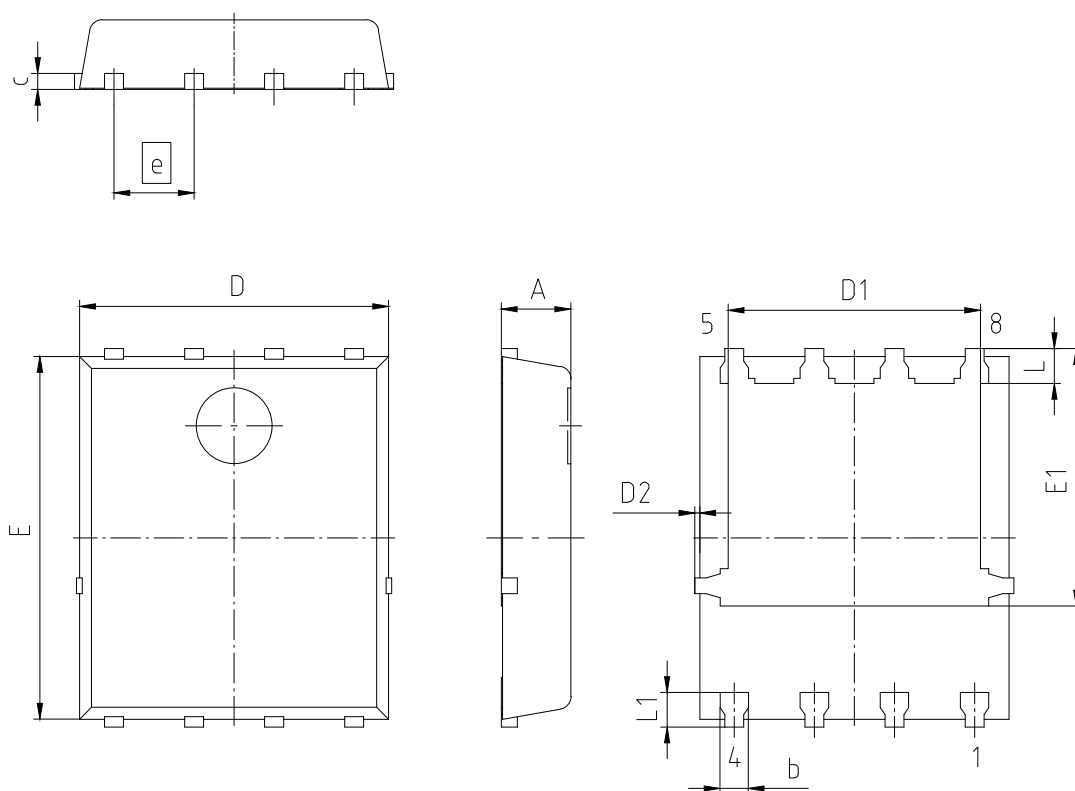


$I_{DSS}=f(V_{DS})$; $V_{GS}=0\text{ V}$; parameter: T_j

Diagram Gate charge waveforms



5 Package Outlines

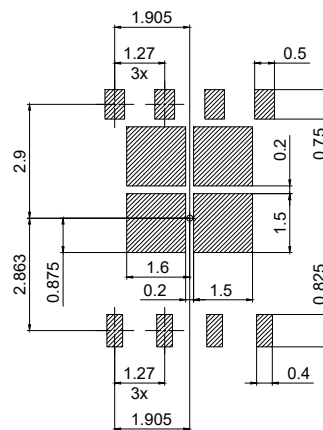
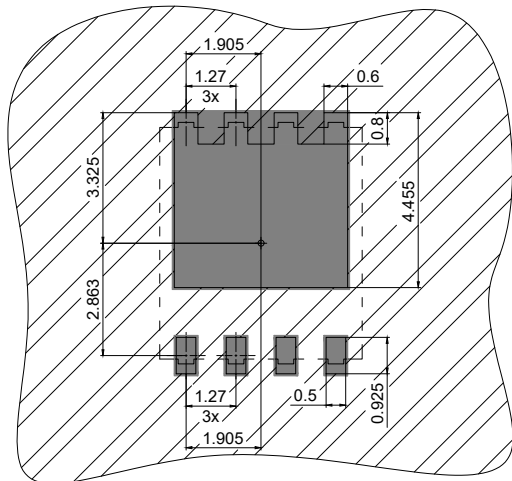


PACKAGE - GROUP NUMBER: PG-TDSON-8-U08		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
b	0.34	0.54
c	0.15	0.35
D	4.80	5.35
D1	3.90	4.40
D2	0.00	0.22
E	5.70	6.10
E1	4.05	4.25
e	1.27	
L	0.45	0.65
L1	0.45	0.65

- 1) EXCLUDING MOLD FLASH
- 2) REMOVAL ON MOLD GATE
INTRUSION 0.1 MM
PROTRUSION 0.1 MM
- 3) ALL METAL SURFACES ARE PLATED,
EXCEPT AREA OF CUT

Figure 1 Outline PG-TDSON-8, dimensions in mm

PG-TDSON-8: Recommended Boardpads & Apertures



copper



solder mask



stencil apertures

all dimensions in mm

Figure 2 Outline Boardpads (TDSON-8), dimensions in mm



Rev. 2.5, 2023-10-02

Revision History

BSC011N03LSI

Revision: 2023-10-02, Rev. 2.5

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.3	2020-02-19	Update package drawings and footnotes
2.4	2020-11-13	Update current rating
2.5	2023-10-02	Update package outline drawing

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